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Team Nexperia

PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

Rev. 5 — 21 December 2011

Product data sheet

1. Product profile

1.1 General description

PNP/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1.	Product	overview

Type number	Package		-		Package
	NXP	JEITA	complement	complement	configuration
PEMB18	SOT666	-	PEMD18	PEMH18	ultra small and flat lead
PUMB18	SOT363	SC-88	PUMD18	PUMH18	very small

Reduces component count

AEC-Q101 qualified

Reduces pick and place costs

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
lo	output current		-	-	-100	mA
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		1.7	2.1	2.6	





1

2 3 006aaa212

PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1	001aab555	

3. Ordering information

Table 4. Ordering information Type number Package Name Description Version PEMB18 plastic surface-mounted package; 6 leads SOT666 PUMB18 SC-88 plastic surface-mounted package; 6 leads SOT363

4. Marking

Table 5. Marking codes	
Type number	Marking code ^[1]
PEMB18	6A
PUMB18	B8*

[1] * = placeholder for manufacturing site code

PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

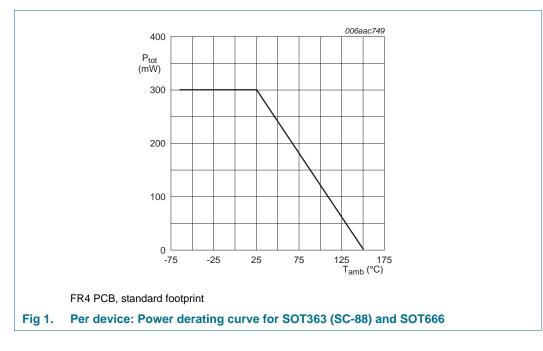
5. Limiting values

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	stor					
V _{CBO}	collector-base voltage	open emitter		-	-50	V
V _{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
VI	input voltage					
	positive			-	+7	V
	negative			-	-20	V
lo	output current			-	-100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$				
	PEMB18 (SOT666)		[1][2]	-	200	mW
	PUMB18 (SOT363)		<u>[1]</u>	-	200	mW
Per device	;					
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$				
	PEMB18 (SOT666)		[1][2]	-	300	mW
	PUMB18 (SOT363)		<u>[1]</u>	-	300	mW
Т _ј	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	+150	°C
T _{stg}	storage temperature			-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω



6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per transistor						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	PEMB18 (SOT666)		<u>[1][2]</u> _	-	625	K/W
	PUMB18 (SOT363)		<u>[1]</u> _	-	625	K/W
Per devic	e					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	PEMB18 (SOT666)		[1][2] _	-	417	K/W
	PUMB18 (SOT363)		<u>[1]</u> _	-	417	K/W

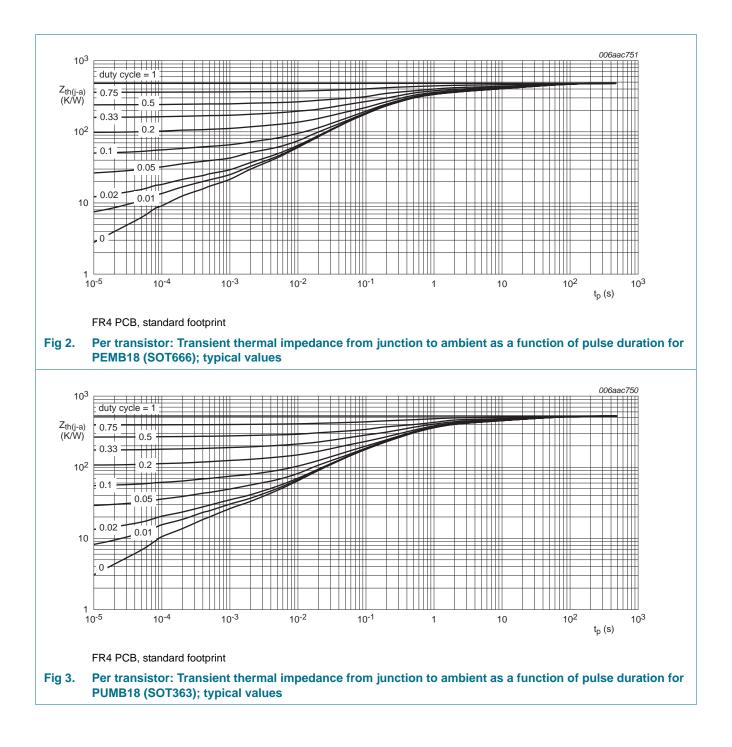
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PEMB18_PUMB18 Product data sheet

PEMB18; PUMB18

PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω



PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

7. Characteristics

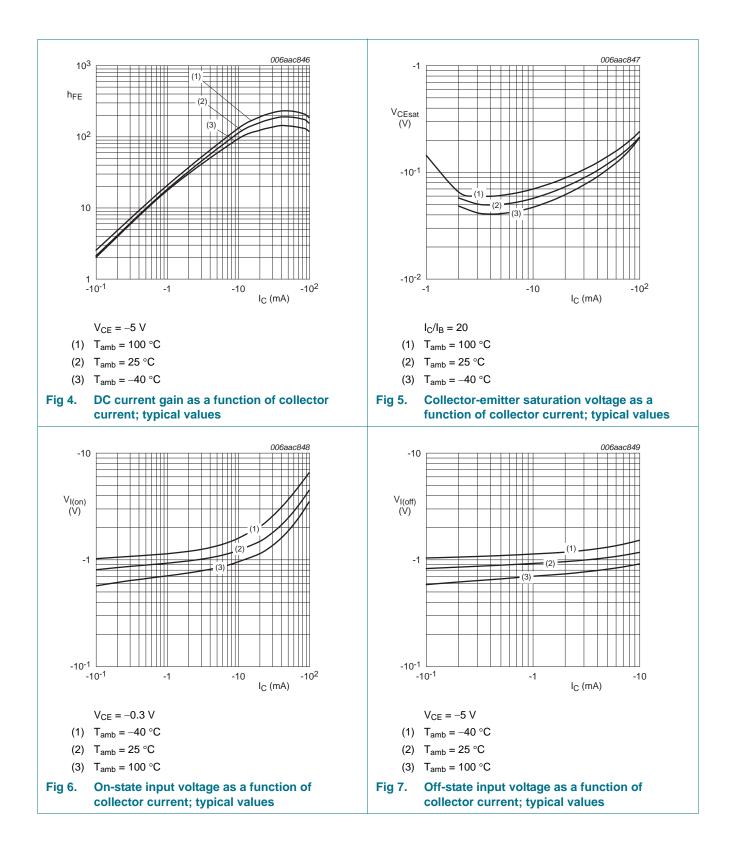
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter cut-off	V_{CE} = -30 V; I _B = 0 A	-	-	-1	μΑ
	current	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A};$ T _j = 150 °C	-	-	-5	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-600	μA
h _{FE}	DC current gain	V_{CE} = -5 V; I _C = -10 mA	50	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -10 \text{ mA}; I_{B} = -0.5 \text{ mA}$	-	-	-100	mV
V _{I(off)}	off-state input voltage	V_{CE} = –5 V; I_{C} = –100 μA	-	-0.9	-0.3	V
V _{I(on)}	on-state input voltage	$V_{CE} = -0.3 \text{ V};$ $I_C = -20 \text{ mA}$	-2.5	-1.5	-	V
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		1.7	2.1	2.6	
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f _T	transition frequency	$V_{CE} = -5 V; I_C = -10 mA;$ f = 100 MHz	<u>1]</u> _	180	-	MHz

[1] Characteristics of built-in transistor

PEMB18_PUMB18 Product data sheet

PEMB18; PUMB18

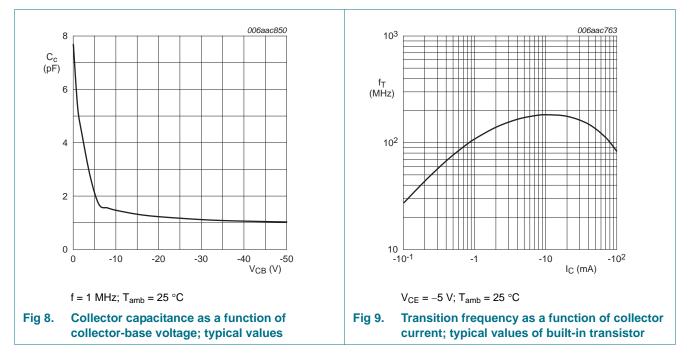
PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω



PEMB18_PUMB18 Product data sheet

PEMB18; PUMB18

PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

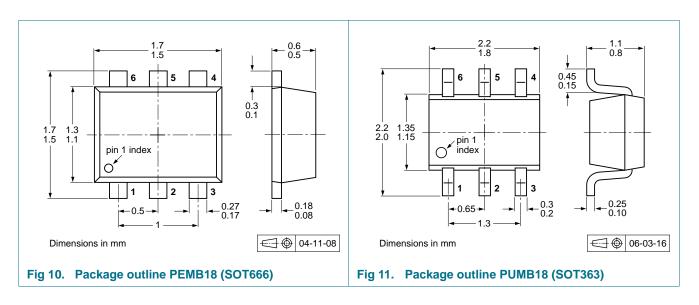


8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



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PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

10. Packing information

Table 9. Packing methods

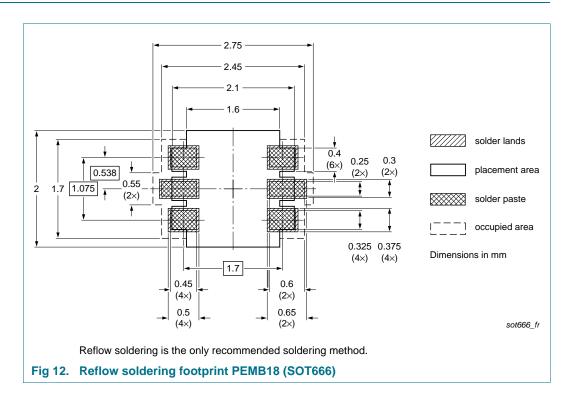
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Туре	Package Description			Packing quantity				
number				3000	4000	8000	10000	
PEMB18	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-	
		4 mm pitch, 8 mm tape and reel		-	-115	-	-	
PUMB18	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135	
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165	

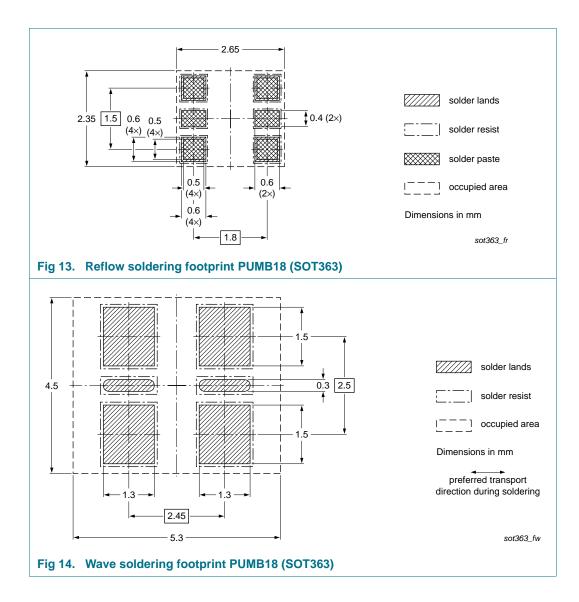
[1] For further information and the availability of packing methods, see Section 14.

- [2] T1: normal taping
- [3] T2: reverse taping

11. Soldering



PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω



PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

12. Revision history

Table 10.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMB18_PUMB18 v.5	20111221	Product data sheet	-	PEMB18_PUMB18 v.4
Modifications:	 Section 4 "M Figure 1 to 3 Section 6 "TI Figure 4 to 7 Table 8 "Cha Section 8 "Te Section 11 "S 	roduct profile": updated arking": updated bermal characteristics": up c updated <u>aracteristics"</u> : I _{CEO} and V _{CE} est information": added <u>Soldering</u> ": added <u>Legal information</u> ": updated	_{isat} updated, f _T added	
PEMB18_PUMB18 v.4	20090901	Product data sheet	-	PEMB18_PUMB18 v.3
PEMB18_PUMB18 v.3	20050708	Product data sheet	-	PEMB18_PUMB18 v.2
PEMB18_PUMB18 v.2	20050202	Product data sheet	-	PUMB18 v.1
PUMB18 v.1	20031003	Product specification	-	-

PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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PEMB18_PUMB18

PNP/PNP resistor-equipped transistors; $R1 = 4.7 \text{ k}\Omega$, $R2 = 10 \text{ k}\Omega$

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PEMB18; PUMB18

PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

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